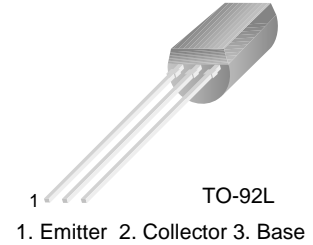


■■ APPLICATION: High Voltage Applications.

■■ MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$


■■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	80		240		$V_{CE} = -5\text{V}$, $I_C = -100\text{mA}$
Collector Cut-off Current	I_{CBO}			-0.1	μA	$V_{CB} = -120\text{V}$, $I_E = 0$
Emitter Cut-off Current	I_{EBO}			-0.1	μA	$V_{EB} = -5\text{V}$, $I_C = 0$
Collector-Base Breakdown Voltage	BV_{CBO}	-120			V	$I_C = -1\text{mA}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-120			V	$I_C = -10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E = -1\text{mA}$, $I_C = 0$
Base-Emitter Voltage	V_{BE}			-1	V	$V_{CE} = -5\text{V}$, $I_C = -500\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-1	V	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$
Gain bandwidth product	f_T	50	120		MHz	$I_C = -100\text{mA}$, $V_{CE} = -5\text{V}$
Common Base Output Capacitance	C_{ob}			40	pF	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$

■■ h_{FE} Classification

Classification	O	Y
h_{FE}	80~160	120~240